



SS12F-PJ~SS120F-PJ

Schottky Barrier Diode

Features

- Low power loss, high efficiency
- For surface mounted applications
- High forward surge current capability

SMAF



1.Cathode ————— 2.Anode

Marking Code:

SS12F-PJ : SS12
SS14F-PJ : SS14
SS16F-PJ : SS16
SS18F-PJ : SS18
SS110F-PJ : SS110
SS112F-PJ : SS112
SS115F-PJ : SS115
SS120F-PJ : SS120

Absolute Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

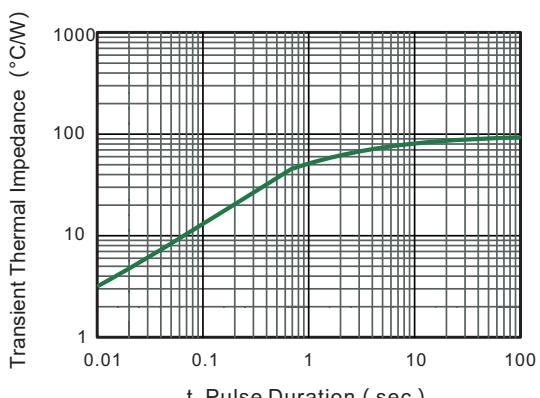
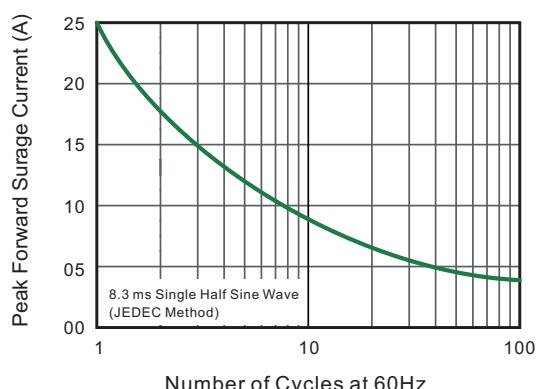
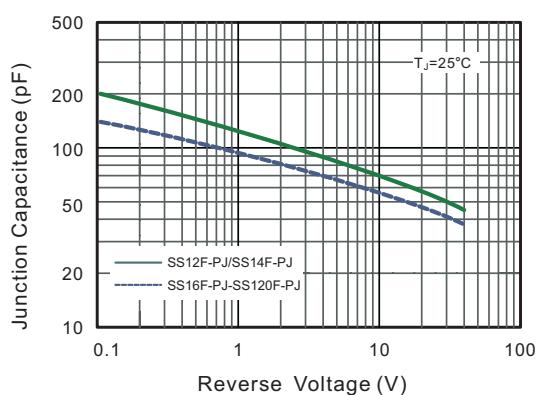
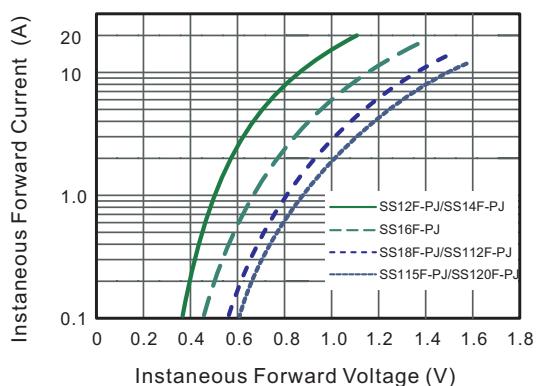
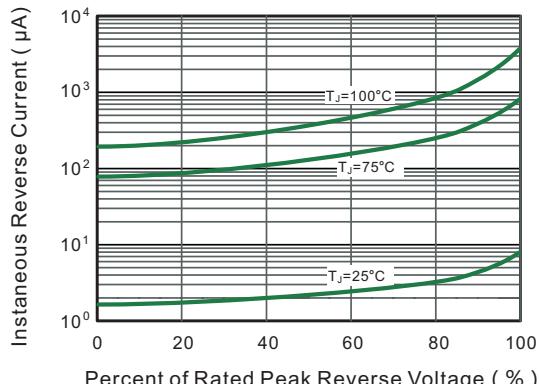
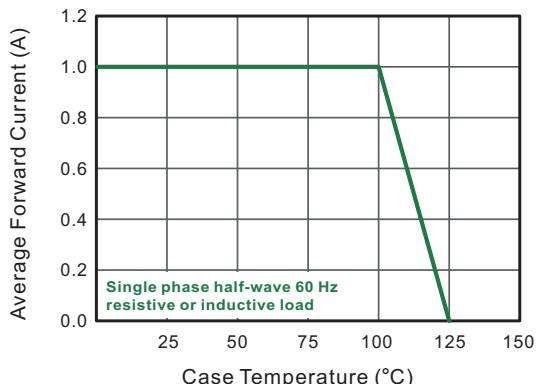
Parameter	Symbol	SS12F-PJ	SS14F-PJ	SS16F-PJ	SS18F-PJ	SS110F-PJ	SS112F-PJ	SS115F-PJ	SS120F-PJ	Unit
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	20	40	60	80	100	120	150	200	V
Maximum RMS Voltage	V _{RMS}	14	28	42	56	70	84	105	140	V
Maximum DC Blocking Voltage	V _{DC}	20	40	60	80	100	120	150	200	V
Maximum Average Forward Rectified Current	I _{F(AV)}					1.0				A
Peak Forward Surge Current,8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}					50				A
Maximum Instantaneous Forward Voltage at 1 A	V _F		0.55		0.70		0.85		0.90	V
Maximum DC Reverse Current at Rated DC Blocking Voltage T _A = 25 °C T _A = 100 °C	I _R		0.3			0.2		0.1		mA
				10			5		2	
Typical Junction Capacitance ^{Note1}	C _j	110				80				pF
Typical Thermal Resistance ^{Note2}	R _{θJA}				95					°C/W
Operating Junction Temperature Range	T _J			-55 to +125						°C
Storage Temperature Range	T _{STG}			-55 to +150						°C

Note:

1. Measured at 1 MHz and applied reverse voltage of 4 V D.C
2. P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.



Typical Characteristic Curves

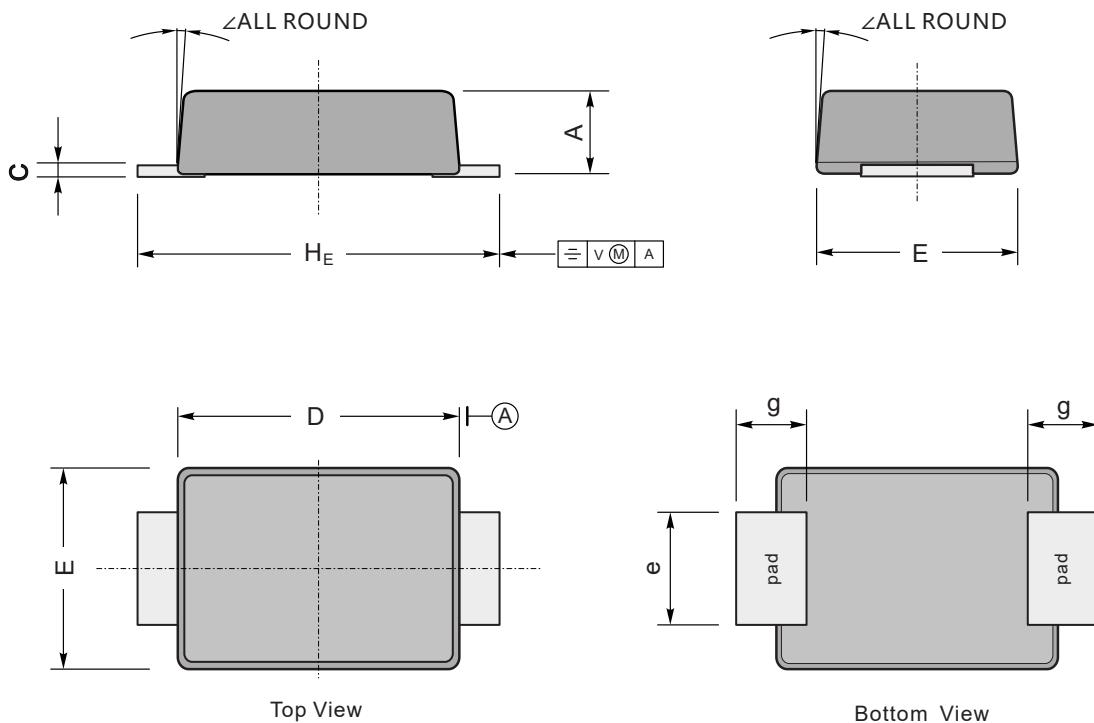




Package Outline

SMAF

Dimensions in mm



UNIT		A	C	D	E	e	g	H _E	∠
mm	max	1.2	0.20	3.7	2.7	1.6	1.2	4.9	7°
	min	0.9	0.12	3.3	2.4	1.3	0.8	4.4	
mil	max	47	7.9	146	106	63	47	193	7°
	min	35	4.7	130	94	51	31	173	